

O I P E  
DEC 22 2003

SHEET 1 OF 4

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210136US99	SERIAL NO. 09/901,109		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Ravindranath DROOPAD, et al.			
		FILING DATE		GROUP			
		July 10, 2001		2815			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
XN		6,233,435 B1	05/15/01	WONG			
XO		4,723,321	02/02/88	SALEH			
XP		6,181,920 B1	01/30/01	DENT ET AL			
XQ		6,415,140 B1	07/02/02	BENJAMIN ET AL			
XR		5,760,740	06/02/98	BLODGETT			
XS		5,238,877	08/24/93	RUSSELL			
XT		4,876,218	10/24/89	PESSA ET AL			
XU		6,232,242 B1	05/15/01	HATA ET AL			
XV		4,378,259	03/29/83	HASEGAWA ET AL			
XW		6,278,541 B1	08/21/01	BAKER			
XY		4,298,247	11/03/81	MICHELET ET AL			
XZ		4,174,504	11/13/79	CHENAUSKY ET AL			
YA		3,758,199	09/11/73	THAXTER			
YB		6,362,558 B1	03/26/02	FUKUI			
YC		6,140,746	10/31/00	MIYASHITA ET AL			
YD		2002/0076878 A1	06/20/02	WASA ET AL			
YE		6,419,849 B1	07/16/02	QIU ET AL			
YF		2002/0179000 A1	12/05/02	LEE ET AL			
YG		6,341,851	01/29/02	TAKAYAMA ET AL			
YH		2001/0055820 A1	12/27/01	SAKURAI ET AL			
YI		6,204,525 B1	03/20/01	SAKURAI ET AL			
YJ		5,985,404	11/16/99	YANO ET AL			
YK		6,538,359 B1	03/25/03	HIRAKU ET AL			
YL		6,498,358 B1	12/24/02	LACH ET AL			
YM		5,387,811	02/07/95	SAIGOH			
YN		5,523,602	06/04/96	HORIUCHI ET AL			
YO		5,362,998	11/08/94	IWAMURA ET AL			
YP		5,188,976	02/23/93	KUME ET AL			
Examiner				Date Considered 2/27/04			

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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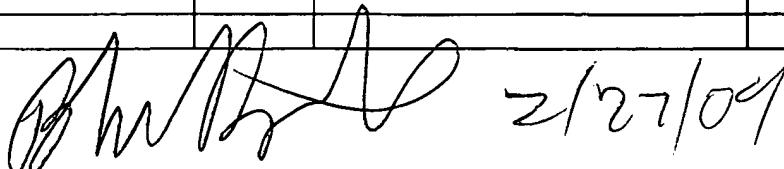
Form PTO 1449 (Modified)  LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 210136US99		SERIAL NO. 09/901,109	
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U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS
bwb	YQ	6,501,121 B1	12/31/02	YU ET AL	
	YR	5,919,515	07/06/99	YANO ET AL	
	YS	5,238,877	08/24/93	RUSSELL	
	YT	5,540,785	07/30/96	DENNARD ET AL	
	YU	5,997,638	12/07/99	COPEL ET AL	
	YV	6,291,866	09/18/01	WALLACE	
	YW	5,365,477	11/15/94	COOPER, JR ET AL	
	YX	5,548,141	08/20/96	MORRIS ET AL	
	YY	2002/0021855	02/21/02	KIM	
	YZ	6,110,840	08/29/00	YU	
	ZA	5,667,586	09/16/97	EK ET AL	
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL	
	ZC	5,315,128	05/24/94	HUNT ET AL	
	ZD	5,919,522	07/06/99	BAUM ET AL	
	ZE	4,843,609	06/27/89	OHYA ET AL	
	ZF	4,626,878	12/02/86	KUWANO ET AL	
	ZG	4,525,871	06/25/85	FOYT ET AL	
	ZH	3,818,451	06/18/74	COLEMAN	
	ZI	6,059,895	05/09/00	CHU ET AL	
	ZJ	4,447,116	05/08/84	KING ET AL	
	ZK	6,022,671	02/08/00	BINKLEY ET AL	
	ZL	5,754,714	05/19/98	SUZUKI ET AL	
	ZM	6,524,651 B2	02/25/03	GAN ET AL	
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL	
	ZO	5,642,371	06/24/97	TOHYAMA ET AL	
	ZP	6,445,724 B2	09/03/02	ABELES	
	ZQ	5,753,934	05/19/98	YANO ET AL	
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL	
	ZS	6,051,874	04/18/00	MASUDA	
	ZT	5,166,761	11/24/92	OLSON ET AL	
	ZU	5,574,744	11/12/96	GAW ET AL	
Examiner				Date Considered 2/27/09	

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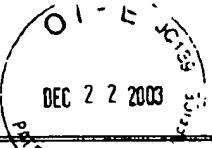
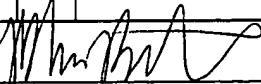
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Ravindranath DROOPAD, et al.			
		FILING DATE July 10, 2001		GROUP 2815	
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES      NO
	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT	
	CCB	2 152 315	07/31/85	GREAT BRITAIN	
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT	
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)	
	CCE	WO 03/012874	02/13/03	WIPO	
	CCF	1 043 427	10/11/00	EUROPE	
	CCG	1 069 605	01/17/01	EUROPE	
	CCH	WO 02/099885	12/12/02	WIPO	
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT	
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)	
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)	
	CCL	WO 02/11254	02/07/02	WIPO	
	CCM	0 494 514	07/15/92	EUROPE	
	CCN	0 247 722	12/02/87	EUROPE	
	CCO	1 037 272	09/20/00	EUROPE	
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)	
	CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT	
	CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT	
	CCS	0 392 714	10/17/90	EUROPE	
	CCT				
	CCU				
	CCV				
	CCW				
	CCX				
	CCY				
	CCZ				
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		<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>	
LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3		
LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001		
LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3		
LLAD	"Holy Graal! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3		
LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO <sub>3</sub> Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651		
LLAF	V. Bomand et al.; "Deposition of LiTaO <sub>3</sub> thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244		
LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296		
LLAH	A.K. Sharma et al.; "Integration of Pb(Zr0.52Ti0.48)O <sub>3</sub> epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460		
LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 Ieee Electron Device Letters; 12(1991) September, No. 9, New York, US		
LLAJ	C. Y. Hung et al; "Piezoelectrically induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US		
LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287		
LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958		
LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246		
LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO <sub>3</sub> at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169		
LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536		
LLAP			
LLAQ			
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